

REPLACEMENT CLAIMS 11, 13, 17, 18

A1 SUB 647

1 11. The parallel plate diode according to claim 1, wherein said metal electrode
2 is made by kovar alloy.

A2

1 13. The parallel plate diode according to claim 1, wherein there are recesses on
2 the surface where the two metal electrodes that make up the parallel plate diode
3 contact the semiconductor material, wherein average diameter of the recesses on
4 one side is equal to or smaller than 0.7 micrometer while the average diameter of the
5 recesses on the other side is bigger than 0.7 micrometer.

A3

1 17. The parallel plate diode according to claim 1, wherein said semiconductor
2 material is liquid semiconductor material.

1 18. The parallel plate diode according to claim 1, wherein said semiconductor
2 material is high resistance metal alloy.

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